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Interest in latchup is being renewed with the evolution of complimentary metal-oxide semiconductor (CMOS) technology, metal-oxide-semiconductor field-effect transistor (MOSFET) scaling, and high-level system-on-chip (SOC) integration. Clear methodologies that grant protection from latchup, with insight into the physics, technology and circuit issues involved, are in increasing demand. This book describes CMOS and BiCMOS semiconductor technology and their sensitivity to present day latchup phenomena, from basic over-voltage and over-current conditions, single event latchup (SEL) and cabl